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		Application Number	10/709,708	3			
TRANSMITTAL		Filing Date	05/24/2004	ļ			
FORM		First Named Inventor	Chien-Hung	Chien-Hung HSU			
(to be used for all correspondence after initial f	Art Unit						
		Examiner Name					
Total Number of Pages in This Submission 3 Attorney Docket Number OTMP0078USA							
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Fee Transmittal Form		Drawing(s)		_l to⊺	Technolo	ance communication ogy Center (TC)	
Fee Attached		Licensing-related Papers		Appeal Communication to Board of Appeals and Interferences Appeal Communication to TC		and Interferences mmunication to TC	
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SIGNA	TURE C	F APPLICANT, ATTORN	EY, OR A	AGENT			
Firm Winston Hsu, Reg. N	No.: 41,	526					
Individual name							
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PTO/SB/17 (10-03)

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FEE TRANSMITTAL for FY 2004

Effective 10/01/2003. Patent fees are subject to annual revision.

Applicant claims small entity status. See 37 CFR 1.27

TOTAL AMOUNT OF PAYMENT

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Complete if Known				
Application Number	10/709,708			
Filing Date	05/24/2004			
First Named Inventor	Chien-Hung HSU			
Examiner Name				
Art Unit				
Attorney Docket No.	OTMP0078USA			

METHOD OF PAYMENT (check all that apply)				FEE	ECALCULATION (continued)	
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The Director is authorized to: (check all that apply)	1053	130	1053		Non-English specification	
Charge fee(s) indicated below Credit any overpayments		2,520	1812	•	For filing a request for ex parte reexamination	
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	1251	110	2251	55	Extension for reply within first month	
FEE CALCULATION	1252	420	2252	210	Extension for reply within second month	
1. BASIC FILING FEE Large Entity Small Entity	1253	950	2253	475	Extension for reply within third month	
Fee Fee Fee Fee Description Fee Paid	1254	1,480	2254	740	Extension for reply within fourth month	
Code (\$) Code (\$) 1001 770 2001 385 Utility filing fee	1255	2,010	2255	1,005	Extension for reply within fifth month	
1002 340 2002 170 Design filling fee	1401	330	2401	165	Notice of Appeal	
1003 530 2003 265 Plant filing fee	1402	330	2402		Filing a brief in support of an appeal	
1004 770 2004 385 Reissue filing fee	1403	290	2403		Request for oral hearing	
1005 160 2005 80 Provisional filing fee	1451	1,510	1451	1,510	Petition to institute a public use proceeding	
SUBTOTAL (1) (\$) 0.00	1452	110	2452	55	Petition to revive - unavoidable	
	1453	1,330	2453	665	Petition to revive - unintentional	
2. EXTRA CLAIM FEES FOR UTILITY AND REISSUE	1501	1,330	2501	665	Utility issue fee (or reissue)	
Extra Claims below Fee Paid	1502	480	2502	240	Design issue fee	
Total Claims 20** = X =	1503	640	2503	320	Plant issue fee	
Claims - 3** = X = 4	1460	130	1460	130	Petitions to the Commissioner	
	1807	50	1807	50	Processing fee under 37 CFR 1.17(q)	
Large Entity Small Entity Fee Fee Fee Fee Fee Description	1806	180	1806		Submission of Information Disclosure Stmt	
Code (\$) Code (\$)	8021	40	8021	40	Recording each patent assignment per property (times number of properties)	
1202 18 2202 9 Claims in excess of 20 1201 86 2201 43 Independent claims in excess of 3	1809	770	2809	385	Filing a submission after final rejection (37 CFR 1.129(a))	
1203 290 2203 145 Multiple dependent claim, if not paid	1810	770	2810	385	For each additional invention to be	
1204 86 2204 43 ** Reissue independent claims over original patent	1801	770	2801	205	examined (37 CFR 1.129(b))	
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SUBMITTED BY						(Complete (if applicable))	
Name (Print/Type)	Winston Hsu	11-	- - 4	Registration No. (Attorney/Agent)	41,526	Telephone 886289237350	
Signature		Was	slos	2 tous		Date \$27/200	7

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DECLARATION — Supplemental Priority Data Sheet

Additional foreign app	lications:			
Prior Foreign Application Number(s)		Foreign Filing Date (MM/DD/YYYY)	Priority Not Claimed	Certified Copy Attached? YES NO
092117396	Taiwan R.O.C	06/25/2003		
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INTELLECTUAL PROPERTY OFFICE MINISTRY OF ECONOMIC AFFAIRS REPUBLIC OF CHINA

茲證明所附文件,係本局存檔中原申請案的副本,正確無訛,

其申請資料如下:

This is to certify that annexed is a true copy from the records of this office of the application as originally filed which is identified hereunder:

申 請 日: 西元 2003 年 06 月 25 日

Application Date

申 請 案 號: 092117396

Application No.

申 請 人: 中強光電股份有限公司

Applicant(s)

局

長

Director General

祭

發文日期: 西元 <u>2004</u> 年 <u>3</u> 月 <u>15</u>日

Issue Date

發文字號: 09320244890

Serial No.





申請日期:	IPC分類	
申請案號:		

(以上各欄	由本局填充	發明專利說明書
	中文	具微結構光學元件之成型方法
發明名稱	英文	Method for forming microstructure optical elements
	(中文)	1. 許建宏 2. 黄文勇 3. 王瑞仁
· - ·	(英文)	1.Chien-Hung Hsu 2.Wen-Yung Huang 3.Ruei-Jen Wang
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	代表人(中文)	1. 張威儀
	代表人(英文)	1. Wade Chang



申請日期:	JIPC分類	
申請案號:		

(以上各欄	由本局填	發明專利說明書
_	中文	
發明名稱	英文	
	姓 名 (中文)	4. 陳佑振 5. 吳家宏
- -		4.Yo-Chen Chen 5.Chia-Hung Wu
發明人 (共5人)	國 籍 (中英文)	4. 中華民國 TW 5. 中華民國 TW
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	名稱或 姓 名 (英文)	
Ξ	國 籍 (中英文)	
申請人(共1人)	住居所 (營業所) (中 文)	
	住居所 (營業所) (英 文)	
	代表人(中文)	
	代表人 (英文)	



四、中文發明摘要 (發明名稱:具微結構光學元件之成型方法)

六、英文發明摘要 (發明名稱:Method for forming microstructure optical elements)

Method for forming microstructure optical elements

The present invention provides a method for forming microstructure optical elements. The method comprises providing a die and forming a cavity in the die according to the shape of microstructure optical elements. The cavity is formed a sealed room, which is evacuated through





四、中文發明摘要 (發明名稱:具微結構光學元件之成型方法)

六、英文發明摘要 (發明名稱:Method for forming microstructure optical elements)

an extraction opening arranged near the end of filling process. Filling materials into the cavity is to be formed the microstructure optical elements. Due to an extraction opening arranged near the end of filling process, the filling process can smooth so as to improve the element quality and manufacturing efficiency.



四、中文發明摘要 (發明名稱:具微結構光學元件之成型方法)

伍、(一)、本案代表圖為:第___3B_____圖

(二)、本案代表圖之元件代表符號簡單說明:

模具21上模211下模212模穴215密封元件216抽氣口22

抽氣孔道 221 澆口 23

六、英文發明摘要 (發明名稱:Method for forming microstructure optical elements)



一、本案已向			\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
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四、□有關微生物已寄存	於國外:		
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□有關微生物已寄存力	於國內(本局所指定	E之寄存機構):	
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寄存號碼: □熟習該項技術者易加	认磁但 工佰宏左。	-	

五、發明說明(1)

【發明所屬之技術領域】

本發明係有關成型方法,尤其係指一種具微結構光學元件之成型方法。

【先前技術】

具微結構光學元件常被廣泛用於光電產品中,例如:液晶顯示器背光模組中之導光板、投影光學系統中之菲涅爾透鏡(Fresnel lens)等,而於講究量產、低成本及高品質之考量下,該光學元件之成型技術頗受到業界重視。

請參閱第1圖及第2圖所示,係習知具微結構光學 元件之成型方法,(A)首先提供一成型模具1112 成型模具111由一公模塊1113於以模塊1112 模塊112間;(B)設置一次以模塊1111 模塊112間;(B)設置一次以閉合成型模 之一端側,並利用一鎖模構(圖未示)以閉合成型 具11;(C)由澆口114注入材料於模穴113 中;(D)待材料固化後,將模具開啟並取出成品。





五、發明說明 (2)

高材料流動性,以縮短填模所需之時間,而提高成品表面品質,但由於材料溫度高,冷卻所需時間增長,將造成總成形時間增加,使生產效率降低;(二)利用提高材料射出速度,但此將使得成品容易產生包氣或噴痕。因此,習知之微結構光學元件之成型方法,仍存在成品表面精度不佳、生產效率低等問題,故有待目前業者提出解決之道。

【發明內容】

本發明之一目的,係提供一種具微結構光學元件之成型方法,利用將抽氣孔設置於模穴充填成型末端,使整個充填過程中可保持模穴之真空度,使填充順利。

本發明之另一目的,係提供一種具微結構光學元件 -之成型方法,抽氣孔經上模、下模、上模仁或下模仁間 之隙縫來抽取模穴內之空氣,以減少廢料產生。

本發明之又一目的,係提供一種具微結構光學元件之成型方法,利用對模穴進行抽真空,以助於材料充填,而提高成品品質、生產效率及轉寫性。

為達上述目的,本發明之具微結構光學元件之成型方法,首先提供一模具,並於模具內依具微結構光學元件形狀形成一模穴,再將模穴形成一密閉空間後,於模穴成型末端附近設一抽氣孔,並透過該抽氣孔對模穴進行抽真空,最後,將材料注入該模穴中成型,以得到具微結構光學元件;由於本發明之成型方法係對模穴進行抽真空且抽氣孔設於成型末端附近,因此,可使材料充





五、發明說明 (3)

填順利,而達到提高成品品質、生產效率以及轉寫性。【實施方式】

有關本發明為達到上述目的,所採用之技術手段及其餘功效,茲舉一較佳實施例,並配合圖式加以說明如下:

3 A 圖 至 第 3 E 圖 所 示 , 本 發 明 具 微 結 構 光學元件之成型方法,其步驟包括:請參閱第3 A 圖所 示,首先,提供一模具2 1,該模具2 1包括一組相對 1 與下模 2 12, 並分別設置一上模仁2 合之上模2 1 3與一下模仁2 1 4 於上模 2 1 1 與下模 2 1 該模仁2 3 \ 2 1 4 可為以電沉積方式形成微結構之 1 金屬薄膜,後於分模面上設置密封元件2 ,該密封 1 6 6 可設於上模 2 1 1 、 下 模 2 1 2或上下模間 1 ,並可增設溝槽 7 以供密封元件2 2 1 16容置 $\cdot 1$ 6 可為 0 型 環 , 請參閱第 3 B 圖 所 示 當 2 關閉後,藉由密封元件 2 1 與下模 2 1 1 6 使 模具21內形成一密閉空間218 (如第 3 C 圖 所 示) ,且於上模仁213與下模仁214間形成模穴2

請參閱第3C圖所示,於密閉空間218內且位於模穴215充填成型末端附近設置抽氣孔22,該抽氣孔226設於上模211與下模212間,並連接一抽氣孔道221,該抽氣孔道221另一端連接一設於模穴215外之真空設備(圖未示),使模穴215經由





五、發明說明(4)

抽氣孔 2 2、抽氣孔道 2 2 1 及真空設備進行抽真空步驟,而維持負壓真空狀態;由於抽氣孔 2 2 之設置位置不直接連接於模穴 2 1 5 ,而透過模具內之隙縫來抽取模穴 2 1 5 內之空氣,故充填過程中可避免材料填充於抽氣孔 2 2 或抽氣孔道 2 2 1 內,因此,可減少廢料產生。

請參閱第3D圖所示,最後,係設置一澆口23於模穴215側邊,且相對抽氣孔22之另一側,由澆口23將材料注入模穴215中成型,其成型方式可為射出成型、鑄造法或轉注成型等方法,後待材料固化後,即打開模具而得到具微結構光學元件成品24(如第3E圖)。

另 外 ,該抽氣孔22及抽氣孔道221可依模具結 横而有不同設計,例如:如第4圖所示,將抽氣孔22 設於或下模仁2 14與下模2 1 2 間,而抽氣孔道22 2 1 設於下模2 1 ;如第 5 圆所示,將抽氣孔22設於 或下模仁2 14與下模2 12間,抽氣孔道22] 設於 下模仁214與下模212;如第6圖所示,模具2 1 增設有滑塊2 9 ,並將抽氣孔22設於滑塊2 - 1 1 9 下模仁214間,抽氣孔道221則設於滑塊219 上模211上。

而材料填充過程中,可藉由抽氣口22將模穴21 5抽真空,使材料流動性增加以助於材料充填,並可使模穴215內之氣體排出,而提高成品品質、生產效率





五、發明說明 (5)

及轉寫性;且該抽氣口22設於充填成型末端,可避免材料於充填過程中遮住抽氣口22而無法抽氣,因此,本發明之成型方法可確保模穴215內於充填過程中均維持真空狀態,而使充填順暢,進而達到提高成品品質及轉寫性。

以上所述,僅用以方便說明本發明之較佳實施例, 本發明之範圍不限於該等較佳實施例,凡依本發明所做 的任何變更,於不脫離本發明之精神下,皆屬本發明申 請專利範圍。



圖式簡單說明

【圖式簡要說明】

第1圖,係習知具微結構光學元件之成型方法流程圖

0

第2圖,係習知具微結構光學元件之成型模具剖視圖

0

第3A圖、第3B圖、第3C圖、第3D圖及第3E

圖,係本發明本發明具微結構光學元件之成型示意圖

0

第4圖、第5圖及第6圖,係本發明成型方法之各種

模具結構配置剖視圖。

【圖號簡要說明】

模具

2 1

上模

2 1 1

下 模

2 1 2

上模仁

2 1 3

下模仁

2 1 4

模穴

2 1 5

密封元件

2 1 6

溝 槽

2 1 7

密閉空間

2 1 8

滑塊

2 1 9

抽氣口

2 2

抽氣孔道

2 2 1

澆 口

2 3



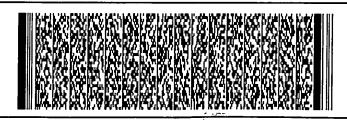
成品

2 4



六、申請專利範圍

- 1、一種具微結構光學元件之成型方法,其步驟包括:
- (A)提供一模具,並於該模具內依據微結構光學元件 形狀形成一模穴;
- (B) 將該模穴形成一密閉空間;
- (C)於該密閉空間內且位於模穴成型末端附近設至少一抽氣孔,並透過該抽氣孔對模穴進行抽氣;以及
- (D) 將材料注入該模穴中成型,以得到具微結構光學 元件。
- 2、如申請專利範圍第1項所述之具微結構光學元件之成型方法,其中步驟(A)中模具包括一上模及一下模,並分別將一上模仁與一下模仁置於上模與下一模內,再關閉上模與下模,以於該上模仁與下模仁間形成該模穴。
- 3、如申請專利範圍第1項所述之具微結構光學元件之成型方法,其中步驟(B)中係利用於模具分模面上設置密封元件以將該模穴形成一密閉空間。
- 4、如申請專利範圍第1項所述之具微結構光學元件之成型方法,其中該該抽氣孔對模穴進行抽氣至真空狀態。
- 5、如申請專利範圍第1項所述之具微結構光學元件之 成型方法,其中該抽氣孔可設於該模仁之四周。
- 6、如申請專利範圍第1項所述之具微結構光學元件之 成型方法,其中該抽氣孔可設於該模具分模面上。

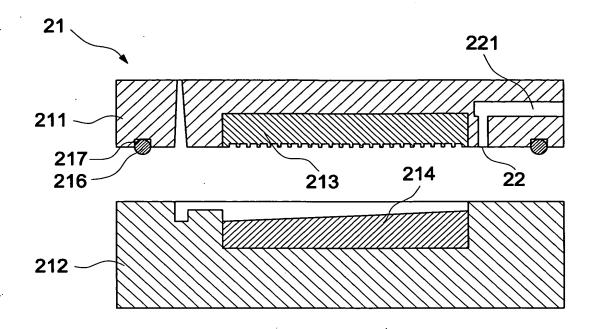


六、申請專利範圍

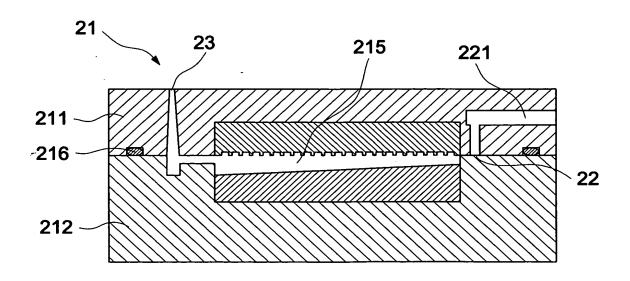
- 7、如申請專利範圍第1項所述之具微結構光學元件之成型方法,其中該抽氣孔可連接一抽氣孔道及一真空設備。
- 8、一種具微結構光學元件之成型模具,其包括:
 - 一組上模與下模,其間形成一模穴;
 - 一密封元件,係設於該上模與下模間,使模穴形成
 - 一密閉空間;以及
 - 一抽氣孔,係設於該模穴充填成型末端附近。
- 9、如申請專利範圍第8項所述之具微結構光學元件之成型模具,其中該模穴內設有一對上模仁與下模仁
- 10、如申請專利範圍第8項所述之具微結構光學元件 之成型模具,其中該密封元件可為0型環。
- 11、如申請專利範圍第8項所述之具微結構光學元件之成型模具,其中該抽氣孔一端設置一抽氣孔道。
- 12、如申請專利範圍第8項所述之具微結構光學元件之成型模具,其中該抽氣孔可設於該模具上下模間
- 13、如申請專利範圍第9項所述之具微結構光學元件之成型模具,其中該抽氣孔可設於上模與上模仁間
- 14、如申請專利範圍第9項所述之具微結構光學元件之成型模具,其中該抽氣孔可設於下模與下模仁間



第门頁

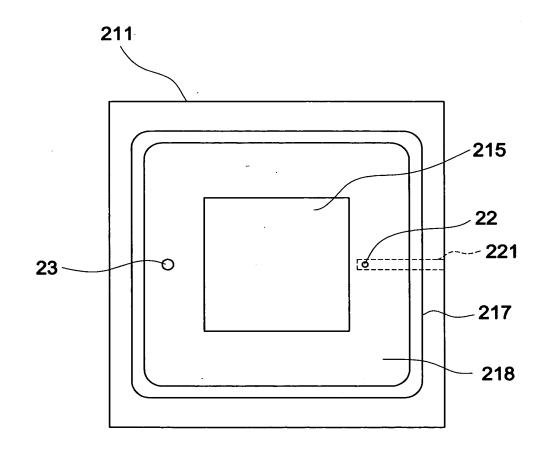


第 3A 圖

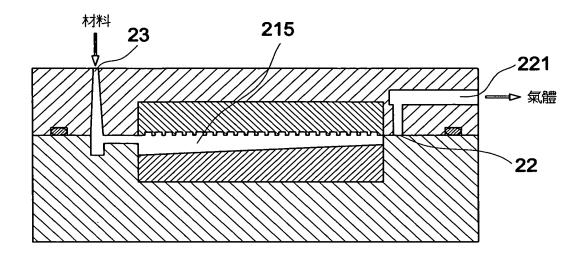


第 3B 圖



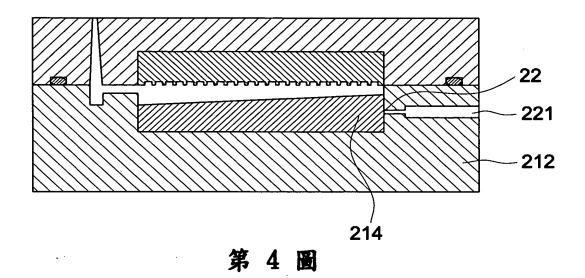


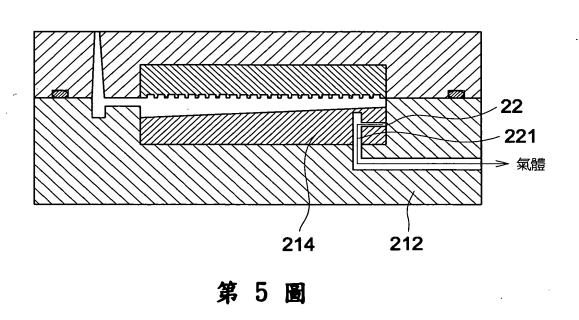
第 3C 圖

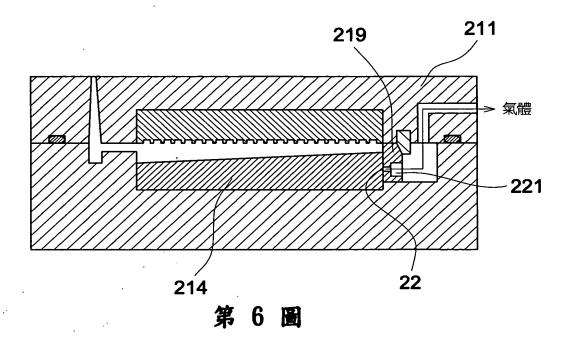


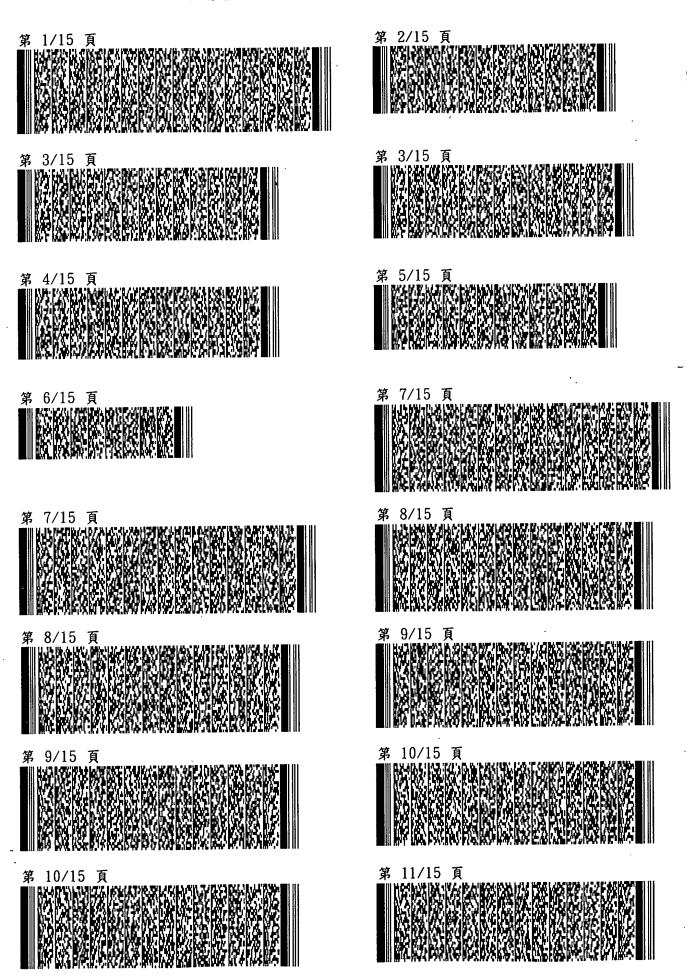
第 3D 圖











(4.5版)申請案件名稱:具微結構光學元件之成型方法







